



General Description

- Trench Power MOSFET - AlphaSGT™ technology
- Extremely Low R_{DS(ON)}
- Optimized switching performance
- 175°C operating temperature
- RoHS and Halogen-Free Compliant

Applications

- Telecom DC-DC
- Industrial power
- Load switch

Product Summary

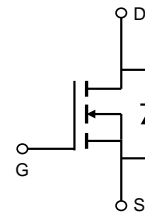
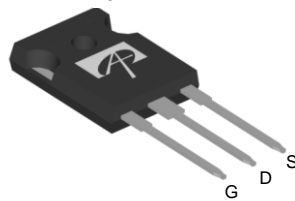
V _{DS}	150V
I _D (at V _{GS} =10V)	120A
R _{DS(ON)} (at V _{GS} =10V)	< 5.4mΩ
R _{DS(ON)} (at V _{GS} =6V)	< 6mΩ

100% UIS Tested
100% R_g Tested

Max T_J=175°C



Top View
TO-247



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOK66518	TO-247	Tube	240

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ^G	I _D	120	A
Current ^G		T _C =25°C	
Pulsed Drain Current ^C	I _{DM}	480	
Continuous Drain Current	I _{DSM}	38	A
		32	
Avalanche Current ^C	I _{AS}	70	A
Avalanche energy	E _{AS}	735	mJ
Power Dissipation ^B	P _D	500	W
		250	
Power Dissipation ^A	P _{DSM}	18	W
		13	
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	R _{θJA}	5	8	°C/W
Maximum Junction-to-Ambient ^{A,D}		t ≤ 10s		
Maximum Junction-to-Case	R _{θJC}	0.22	0.30	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	150			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =150V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2.7	3.2	3.7	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		4.5 7.8	5.4 9.5	mΩ
		V _{GS} =8V, I _D =20A		4.8	6.0	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		50		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current ^G				120	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =75V, f=1MHz		6460		pF
C _{oss}	Output Capacitance			820		pF
C _{riss}	Reverse Transfer Capacitance			5		pF
R _g	Gate resistance	f=1MHz	1.1	2.3	3.5	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =75V, I _D =20A		80	115	nC
Q _{gs}	Gate Source Charge			32		nC
Q _{gd}	Gate Drain Charge			15		nC
Q _{oss}	Output Charge	V _{GS} =0V, V _{DS} =75V		273		nC
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =75V, R _L =2.5Ω, R _{GEN} =3Ω		27		ns
t _r	Turn-On Rise Time			20		ns
t _{D(off)}	Turn-Off Delay Time			49		ns
t _f	Turn-Off Fall Time			28		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=500A/μs		86		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=500A/μs		920		nC

- A. The value of R_{θJA} is measured in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 175° C. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on T_{J(MAX)}=175° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Single pulse width limited by junction temperature T_{J(MAX)}=175° C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175° C. The SOA curve provides a single pulse rating.
- G. The maximum current rating is package limited.
- H. These tests are performed in a still air environment with T_A=25° C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

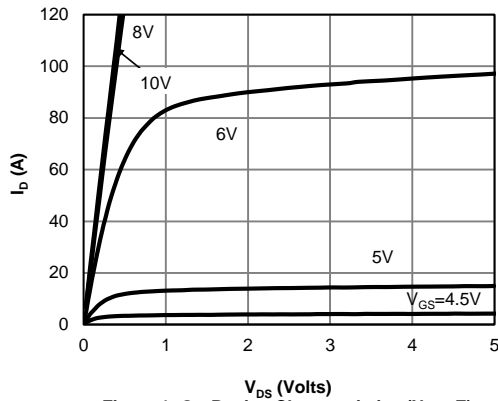


Figure 1: On-Region Characteristics (Note E)

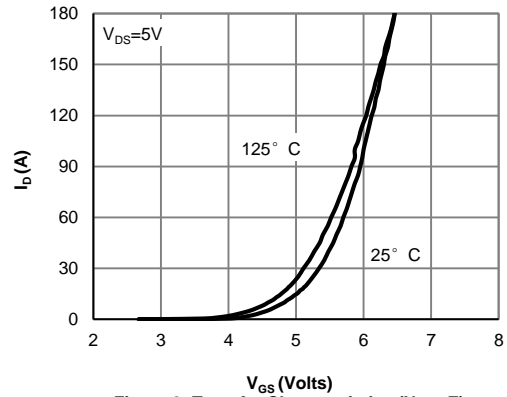


Figure 2: Transfer Characteristics (Note E)

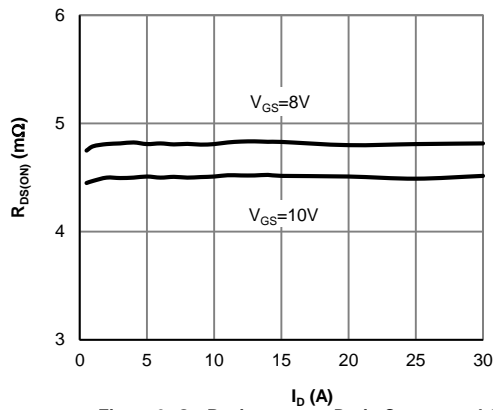


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

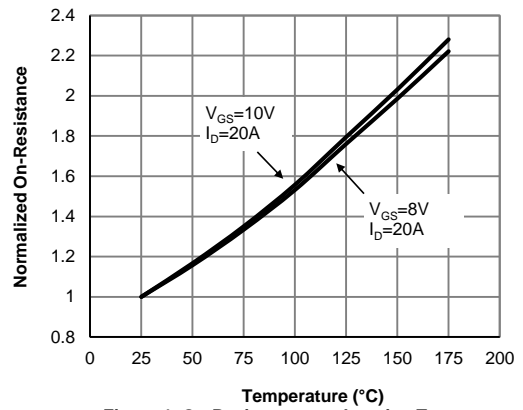


Figure 4: On-Resistance vs. Junction Temperature (Note E)

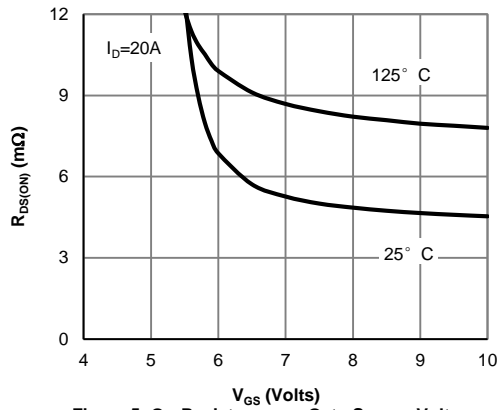


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

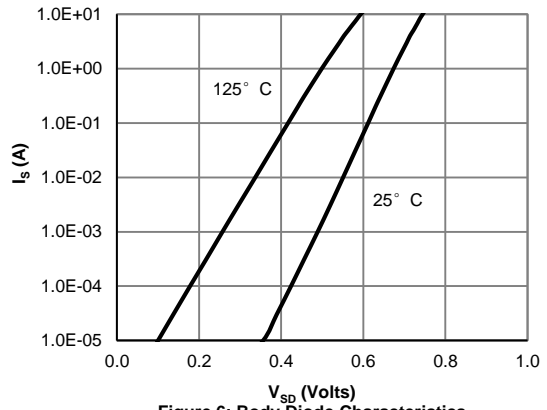


Figure 6: Body-Diode Characteristics (Note E)

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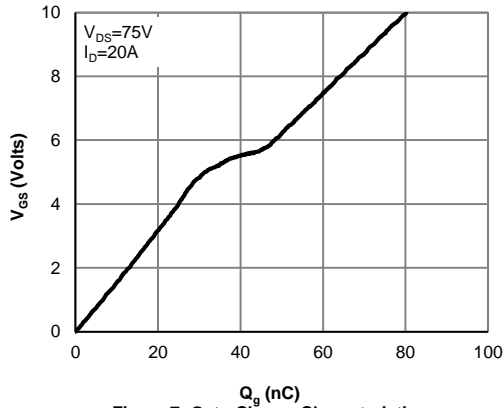


Figure 7: Gate-Charge Characteristics

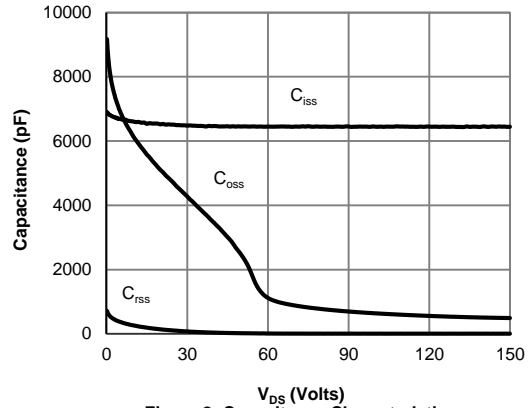


Figure 8: Capacitance Characteristics

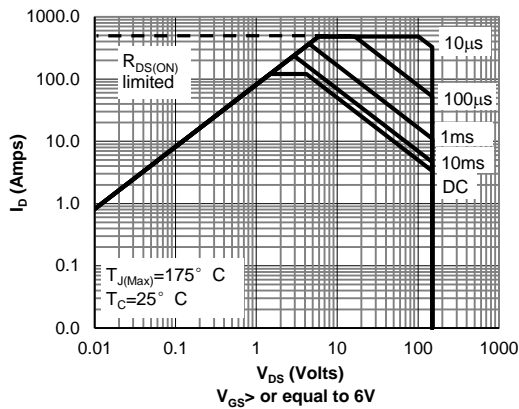


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

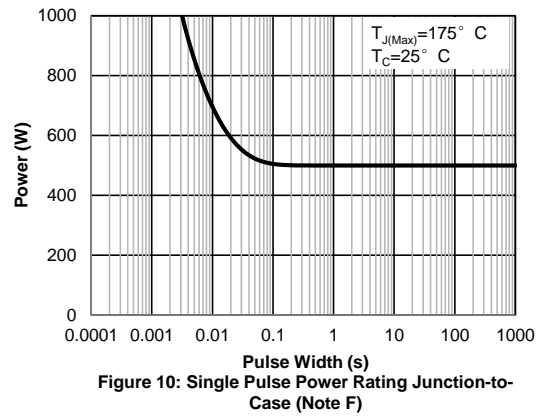


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

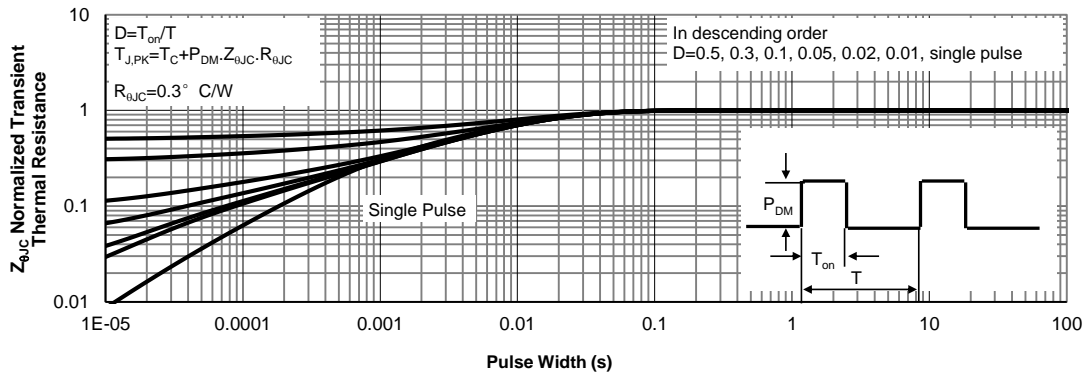


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

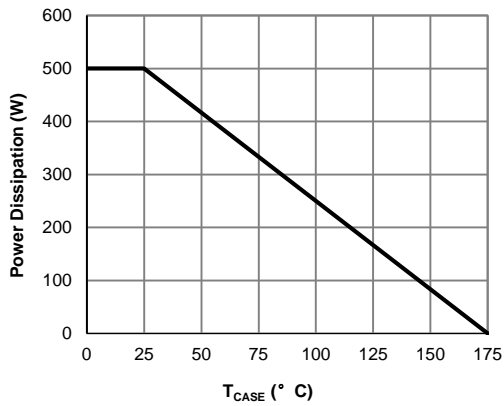


Figure 12: Power De-rating (Note F)

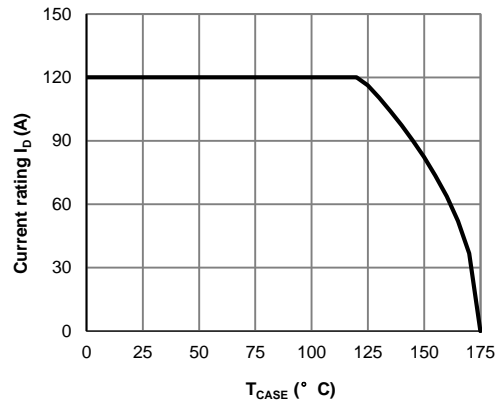


Figure 13: Current De-rating (Note F)

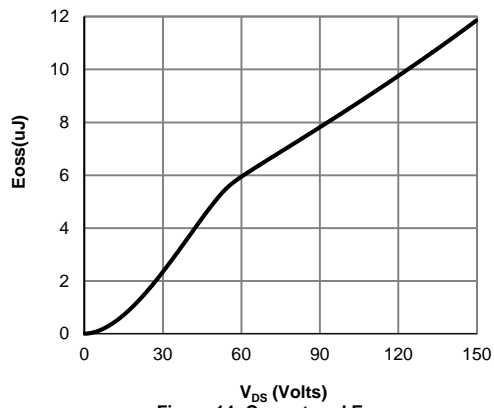


Figure 14: Coss stored Energy

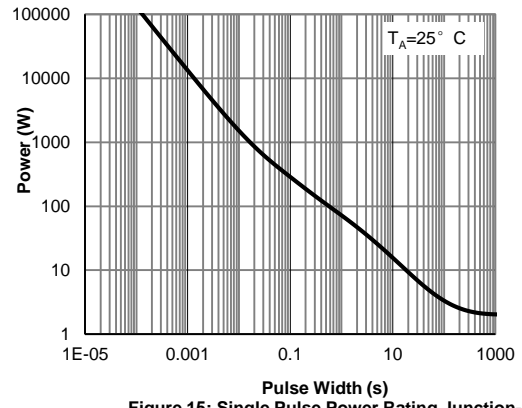


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

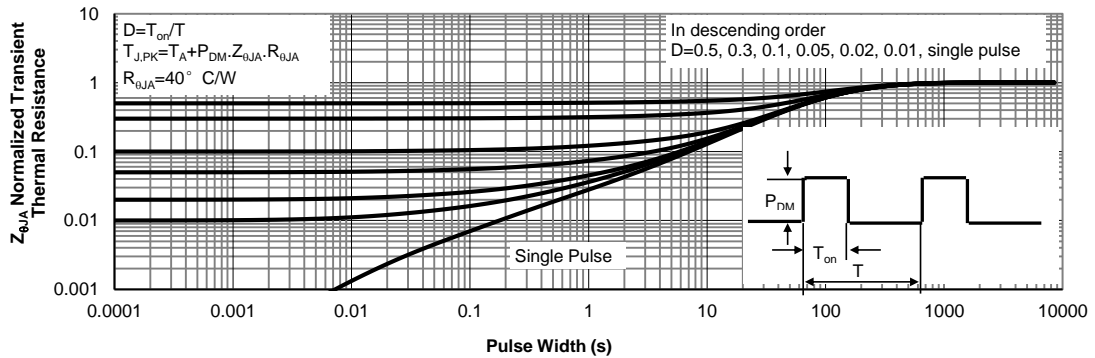


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

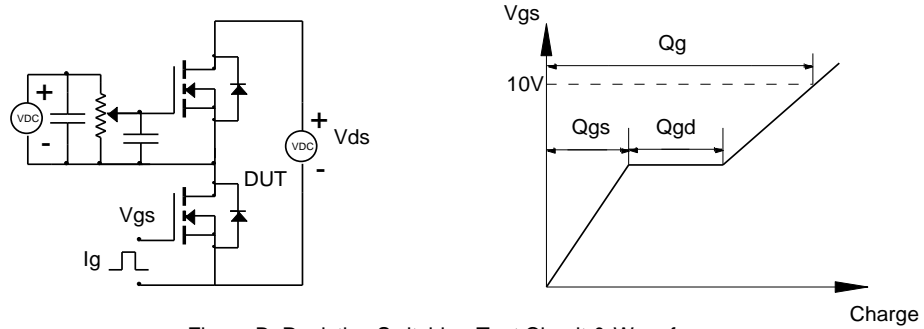


Figure B: Resistive Switching Test Circuit & Waveforms

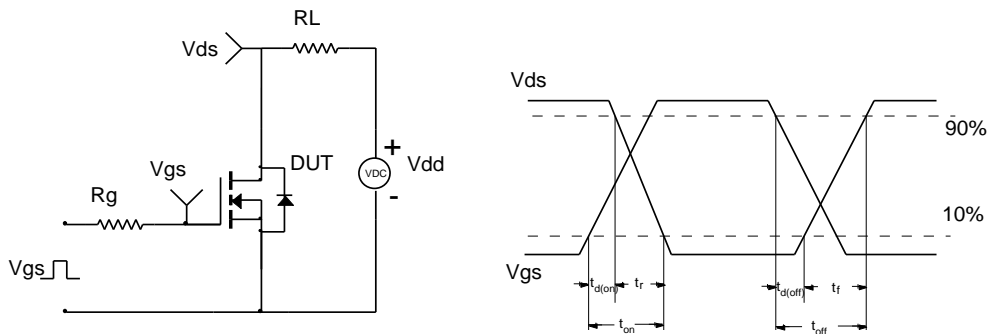


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

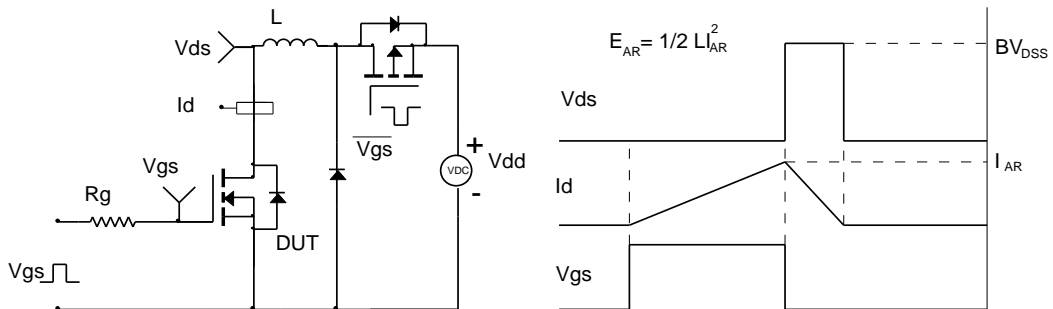


Figure D: Diode Recovery Test Circuit & Waveforms

